

## ZXMN0545G4

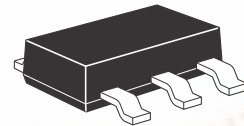
### 450V N-CHANNEL ENHANCEMENT MODE MOSFET

#### SUMMARY

$V_{(BR)DSS} = 450V$ ;  $R_{DS(ON)} = 50\Omega$ ;  $I_D = 140mA$

#### DESCRIPTION

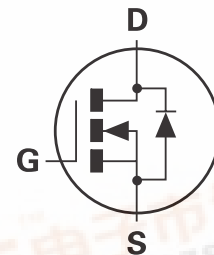
This 450V enhancement mode N-channel MOSFET provides users with a competitive specification offering efficient power handling capability, high impedance and is free from thermal runaway and thermally induced secondary breakdown. Applications benefiting from this device include a variety of Telecom and general high voltage circuits.



SOT223

#### FEATURES

- High voltage
- Low on-resistance
- Fast switching speed
- Low gate drive
- Low threshold
- SOT223 package variant engineered to increase spacing between high voltage pins

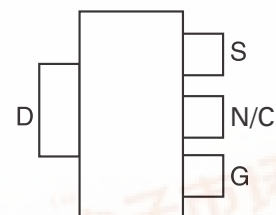


#### APPLICATIONS

- Off-line power supply start-up circuitry

#### ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXMN0545G4TA	7	12mm embossed	1,000 units
ZXMN0545G4TC	13	12mm embossed	4,000 units



PINOUT - TOP VIEW

#### DEVICE MARKING

ZXMN  
0545

# ZXMN0545G4

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	$V_{DS}$	450	V
Gate Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $V_{GS}=10V$ ; $T_{amb}=25^{\circ}C$ ) <sup>(a)</sup>	$I_D$	140	mA
Pulsed Drain Current <sup>(c)</sup>	$I_{DM}$	600	mA
Continuous Source Current (Body Diode) <sup>(b)</sup>	$I_S$	140	A
Pulsed Source Current (Body Diode) <sup>(c)</sup>	$I_{SM}$	600	A
Power Dissipation at $T_{amb}=25^{\circ}C$ <sup>(a)</sup>	$P_{tot}$	2.0	W
Linear derating factor		1.6	mW/ $^{\circ}C$

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient <sup>(a)</sup>	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Junction to Ambient <sup>(b)</sup>	$R_{\theta JA}$	32	$^{\circ}C/W$

### NOTES:

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at  $t \leq 5$  secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

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### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS
Drain-Source Breakdown Voltage	$BV_{DSS}$	450		V	$I_D = 1\text{mA}$ , $V_{GS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1	3	V	$I_D = 1\text{mA}$ , $V_{DS} = V_{GS}$
Gate-Body Leakage	$I_{GSS}$		20	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$		10 400	$\mu\text{A}$ $\mu\text{A}$	$V_{DS} = 450\text{V}$ , $V_{GS} = 0\text{V}$ $V_{DS} = 405\text{V}$ , $V_{GS} = 0\text{V}$ , $T = 125^{\circ}\text{C}$ (2)
On-State Drain Current (1)	$I_{D(on)}$	150		mA	$V_{DS} = 25\text{V}$ , $V_{GS} = 10\text{V}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		50	$\Omega$	$V_{GS} = 10\text{V}$ , $I_D = 100\text{mA}$
Forward Transconductance (1)(2)	$g_{fs}$	100		mS	$V_{DS} = 25\text{V}$ , $I_D = 100\text{mA}$
Input Capacitance (2)	$C_{iss}$		70	pF	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$
Common Source Output Capacitance (2)	$C_{oss}$		10	pF	
Reverse Transfer Capacitance (2)	$C_{rss}$		4	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	$V_{DD} = 25\text{V}$ , $I_D = 100\text{mA}$
Rise Time (2)(3)	$t_r$		7	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		16	ns	
Fall Time (2)(3)	$t_f$		10	ns	

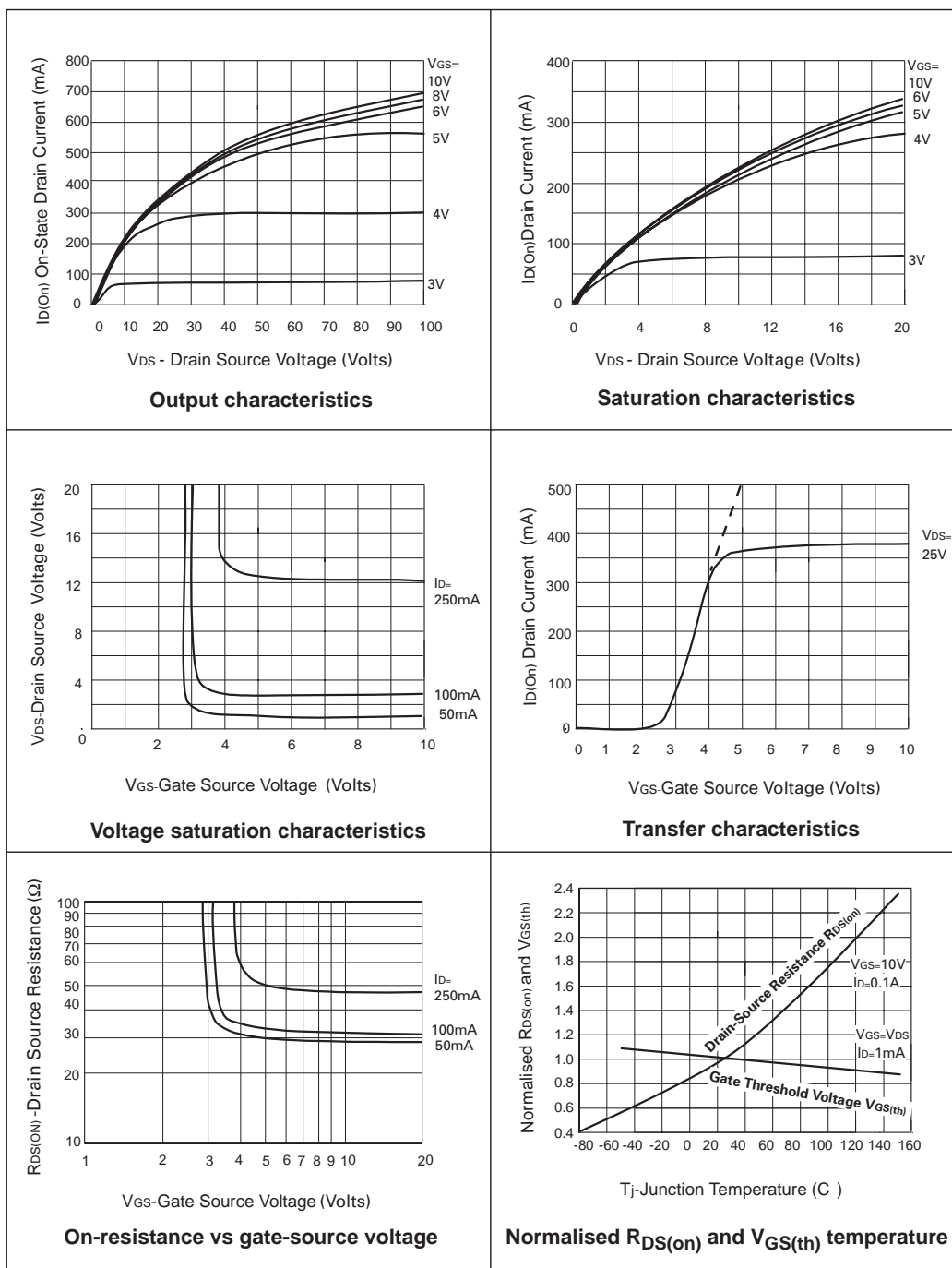
(1) Measured under pulsed conditions. Width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

(2) Sample test.

(3) Switching times measured with 50 $\Omega$  source impedance and <5ns rise time on a pulse generator

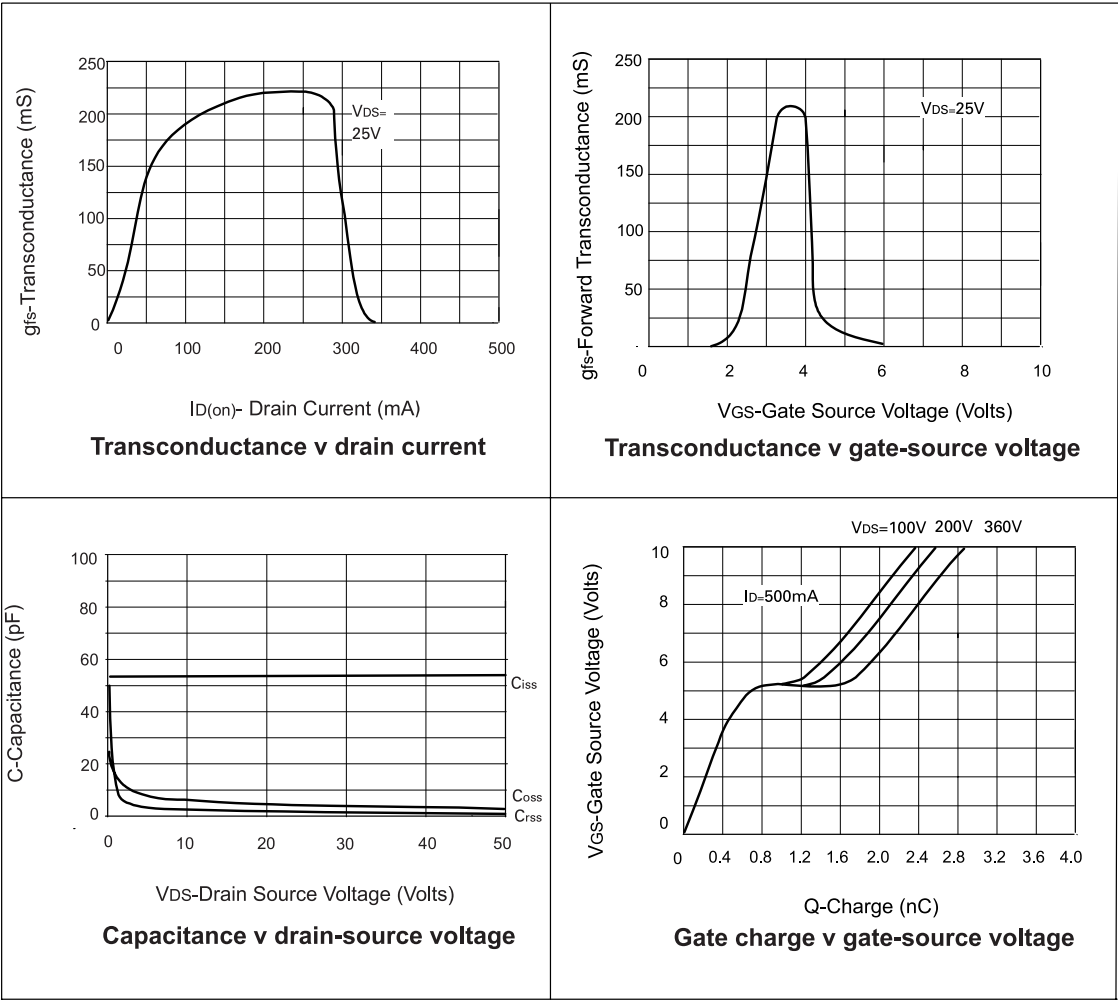
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## TYPICAL CHARACTERISTICS



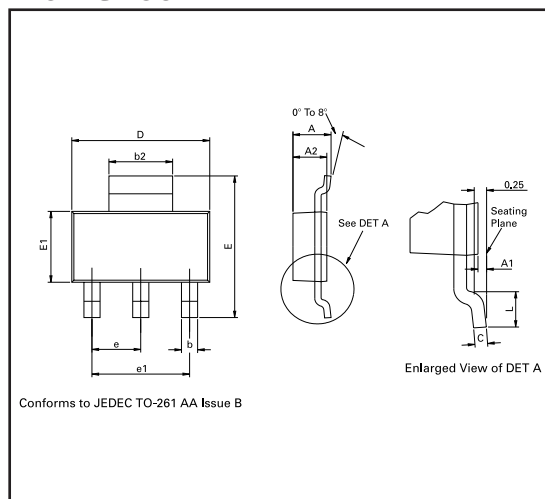
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TYPICAL CHARACTERISTICS

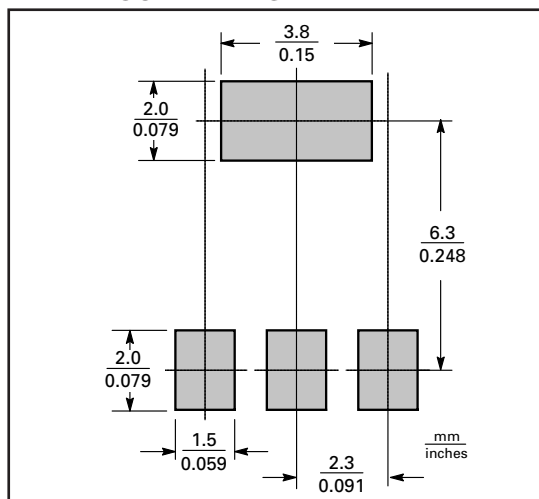


# ZXMN0545G4

## PACKAGE OUTLINE



## PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

## PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

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